## Ultrathin Co-O oxide layer-driven perpendicular magnetic anisotropy in a $\label{eq:coO/Co/Pd} \text{CoO/[Co/Pd]}_m \text{ multilayer matrix upon annealing}$

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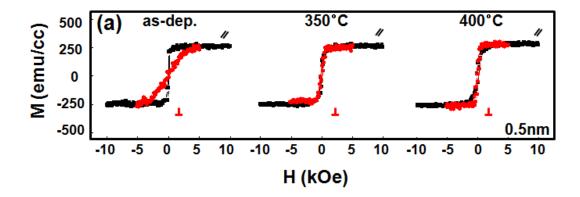
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**Supplementary Information** 

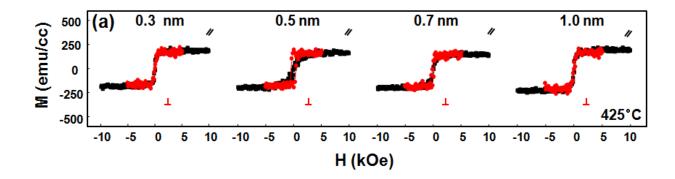
## 1. Magnetic hysteresis loops of the as-grown and annealed Co capping without oxygen insertion (Stack A)

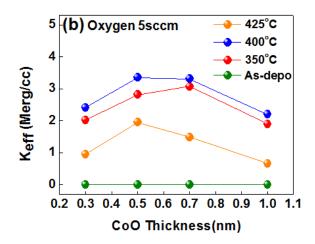
As shown in Fig. S1, Stack A with a Co capping layer containing no oxygen exhibited no clear PMA regardless of annealing, in which in-plane dominant magnetization was obtained without particular change.



**Fig. S1.** Magnetic hysteresis loops of as-grown, 350°C, and 400°C-annealed Stack A, where the Co capping thickness was  $t_{co}$ = 0.5 nm

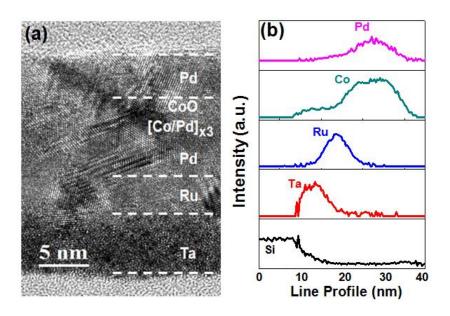
## 2. Magnetic hysteresis loops and $K_{eff}$ value of 425°C-annealed Stack B





**Fig. S2.** (a) Magnetic hysteresis loops of 425°C-annealed Stack B, where the Co capping thickness was  $t_{CoO}$ = 0.3 ~ 1.0 nm, (b) effective magnetic anisotropy energy ( $K_{eff}$ ) for as-grown (green line), 350°C (red line), 400°C (blue line), and 425°C (orange line) post-annealed Stack B samples as a function of CoO thickness.

## 3. TEM images and corresponding EDS analyses of 350°C-annealed Stack B



**Fig. S3.** (a) TEM images and (b) corresponding EDS analyses of 350°C-annealed Stack B, in which oxygen was not detected due to the extremely small amount of oxygen inside the CoO capping layer and significant out-diffusion during annealing.